

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : TBD
 Applicant : Yuichiro Sasaki et al.
 Filed : Herewith
 Title : "METHOD FOR MAKING JUNCTION AND
 PROCESSED MATERIAL FORMED USING THE SAME"

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 Examiner : TBD

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 Docket No. : 40201

INFORMATION DISCLOSURE STATEMENT

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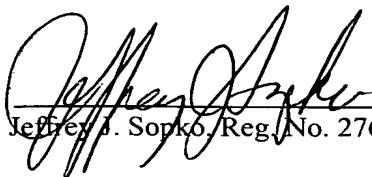
Sir/Madam:

In accordance with Rule 56, applicants are aware of the publications listed in the International Search Report (ISR, copy enclosed) and in the enclosed copy of Patent Office Form 1449. Copies of the publications cited in the International Search Report are not enclosed as they were previously forwarded by the International Bureau, however, a copy of each publication cited in the specification is enclosed.

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Respectfully submitted,

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INFORMATION DISCLOSURE CITATION BY APPLICANT <i>(USE SEVERAL SHEETS IF NECESSARY)</i>		APPLICANT: Yuichiro Sasaki et al.	
		FILING DATE: Herewith	GROUP ART UNIT: TBD

U.S. PATENT DOCUMENTS							
Examiner Initial		Document No.	Date	Name	Class	Subclass	Filing Date If Appropriate
	A						
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FOREIGN PATENT DOCUMENTS							
		Document No.	Date	Country	Class	Subclass	Translation
	H	5-206053	08/1993	JAPAN			Cited on ISR
	I	9-17867	01/1997	JAPAN			Cited on ISR
	J	2003-528462	09/2003	JAPAN			Cited on ISR
	K						

OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
L	Talwar et al., "Study of Laser Thermal Processing (LPT) to Meet Sub 130 nm Node Shallow Junction Requirements", 2000, pages 175-177 (Cited in Specification)
M	Ito et al., "Flash Lamp Annealing Technology for Ultra-shallow Junction Formation", Extended Abstract of International Workshop on Junction Technology, 2002, pages 23-26 (Cited in Specification)
N	Yamamoto et al., "Impact of Pre-Amorphization for the Reduction of Contact Resistance Using Laser Thermal Process", Extended Abstract of International Workshop on Junction Technology, 2002, pages 27-30 (Cited in Specification)
O	Kagawa et al., "Influence of Pulse Duration on KrF Excimer Laser Annealing Process for Ultra Shallow Junction Formation, Extended Abstract of International Workshop on Junction Technology, 2002, pages 31-34 (Cited in Specification)
P	Ito et al., "Improvement of Threshold Voltage Roll-off by Ultra-shallow Junction Formed by Flash Lamp Annealing", 2003, pages 53-54 (Cited in Specification)

Examiner:	Date Considered
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